

Customer No.: 31561

Application No.: 10/604,627

Docket No.: 11112-US-PA

**ABSTRACT AMENDMENT**

Please amend the Abstract as indicated hereafter:

The present invention provides a resistance random access memory structure, ~~comprising~~including a plurality of word lines in a substrate, a plurality of reset lines  
5 coupled to the word lines, a dielectric layer on the substrate, a plurality of memory units  
in the dielectric layer. Each of the memory units includes a bottom electrode, a top  
electrode and a resistive thin film between the top electrode and the bottom electrode.  
The top electrodes of the memory units in a same column are coupled to one of the reset  
lines and a plurality of the bit lines on the memory units. The bottom electrodes of the  
10 memory units in a same row are coupled to one of the bit lines. Because the present  
invention provides reset lines for Type 1R1D RRAM, it can overcome the non-erasable  
of the conventional Type 1R1D RRAM.